# Nanoscale Advances

# PAPER

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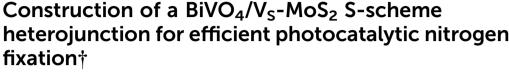
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## 1. Introduction

Ammonia (NH<sub>3</sub>) serves as both a promising energy storage intermediary and an essential raw material affecting agricultural and industrial production.<sup>1,2</sup> However, given the molecular inertness of N<sub>2</sub> (dissociation energy of 945 kJ mol<sup>-1</sup>), the current industrial synthesis of NH<sub>3</sub> predominantly relies on the Haber–Bosch process.<sup>3,4</sup> This traditional method requires high temperature and pressure (300–550 °C and 15–25 MPa), resulting in significant investment costs and high energy consumption.<sup>5,6</sup> Therefore, the pursuit of synthetic processes under mild conditions has become a paramount objective. Photocatalytic N<sub>2</sub> fixation, employing semiconductor photocatalysts that harness sunlight as the energy source while utilizing N<sub>2</sub> and H<sub>2</sub>O as reactants, stands out as a sustainable approach for NH<sub>3</sub> production.<sup>7-10</sup> Nonetheless, because of the poor N<sub>2</sub> adsorption–activation and carrier separation in



Han-Ying Luo,‡<sup>a</sup> Zhao-Lei Liu,‡<sup>a</sup> Meng-Ran Zhang,<sup>a</sup> Yan-Fei Mu<sup>b\*b</sup> and Min Zhang<sup>\*</sup>

Photocatalytic nitrogen (N<sub>2</sub>) reduction to ammonia (NH<sub>3</sub>), adopting H<sub>2</sub>O as the electron source, suffers from low efficiency owing to the sluggish kinetics of N<sub>2</sub> reduction and the requirement of a substantial thermodynamic driving force. Herein, we present a straightforward approach for the construction of an S-scheme heterojunction of BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> to successfully achieve photocatalytic N<sub>2</sub> fixation, which is manufactured by coupling an N<sub>2</sub>-activation component (V<sub>S</sub>-MoS<sub>2</sub> nanosheet) and water-oxidation module (BiVO<sub>4</sub> nanocrystal) through electrostatic self-assembly. The V<sub>S</sub>-MoS<sub>2</sub> nanosheet, enriched with sulfur vacancies, plays a pivotal role in facilitating N<sub>2</sub> adsorption and activation. Additionally, the construction of the S-scheme heterojunction enhances the driving force for water oxidation and improves charge separation. Under simulated sunlight irradiation (100 mW cm<sup>-2</sup>), BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> exhibits efficient photocatalytic N<sub>2</sub> reduction activity with H<sub>2</sub>O as the proton source, yielding NH<sub>3</sub> at a rate of 132.8 µmol g<sup>-1</sup> h<sup>-1</sup>, nearly 7 times higher than that of pure V<sub>S</sub>-MoS<sub>2</sub>. This study serves as a noteworthy example of efficient N<sub>2</sub> reduction to NH<sub>3</sub> under mild conditions.

semiconductor photocatalysts, achieving efficient photocatalytic conversion of  $N_2$  to  $NH_3$  remains a scientific challenge.<sup>11-13</sup>

Efficient N2 adsorption-activation and good light absorption of photocatalysts are the fundamental prerequisites for realizing the efficient photoreduction of N2 to produce NH3.14 Consequently, the initial step involves the selection of potential semiconductor materials to reasonably design photocatalysts with suitable energy levels for N<sub>2</sub> reduction and favorable properties for N2 adsorption-activation.15-17 Schrauzer and coworkers conducted the pioneering systematic investigation into the photocatalytic NH<sub>3</sub> synthesis using TiO<sub>2</sub>-based materials.18 In recent years, numerous studies have explored traditional metal oxides, carbonaceous materials, and layered double hydroxide semiconductors as photocatalysts for N<sub>2</sub> photofixation.<sup>19-22</sup> However, these semiconductor materials often exhibit wide band gaps and narrow spectral absorption characteristics, which are not conducive for efficient photon utilization in photocatalytic reactions. Inspired by the MoFecofactor in natural nitrogenase, molybdenum disulfide  $(MoS_2)$ has garnered significant attention in the field of N2 fixation due to its structural resemblance to nitrogenase with a Mo-S configuration.<sup>23,24</sup> As a two-dimensional direct bandgap semiconductor material, MoS<sub>2</sub> not only possesses good photon capture ability but also can be used as a carrier to construct composite catalysts to achieve more efficient catalytic conversion. Nonetheless, MoS<sub>2</sub> exhibits poor activity in photocatalytic N<sub>2</sub> reduction systems using water as the electron source due to

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<sup>&</sup>lt;sup>a</sup>MOE International Joint Laboratory of Materials Microstructure, Institute for New Energy Materials and Low Carbon Technologies, School of Materials Science and Engineering, School of Chemistry and Chemical Engineering, Tianjin University of Technology, Tianjin 300384, China. E-mail: zm2016@email.tjut.edu.cn

<sup>&</sup>lt;sup>b</sup>School of Chemistry and Chemical Engineering, Yangzhou University, Yangzhou, Jiangsu 225009, China. E-mail: 007916@yzu.edu.cn

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<sup>‡</sup> Han-Ying Luo and Zhao-Lei Liu contributed equally to this work.

its lack of water oxidation capacity.25 In addition, akin to other semiconductor photocatalysts, its weak photogenerated carrier separation ability also hinders the progress of photocatalytic N2 reduction.<sup>26,27</sup> To improve the photocatalytic activity of semiconductor photocatalysts, extensive research efforts have focused on bolstering charge separation through the construction of p-n, II-type, and S-scheme heterojunctions.<sup>28-31</sup> Mimicking natural photosynthesis, the S-scheme charge transfer system has received special attention, which can simultaneously facilitate spatial carrier separation and improve redox ability.<sup>32,33</sup> Additionally, monoclinic BiVO<sub>4</sub> as a "star" material has a broad range of visible light utilization and excellent photoelectric stability, and has been widely used in the study of photoanodic water oxidation.34 Based on this, BiVO4 has potential to serve as a water oxidation unit for MoS<sub>2</sub> to construct heterojunctions, further enhancing the efficiency of photocatalytic N<sub>2</sub> fixation.

Herein, we present an innovative S-scheme heterojunction prepared by coupling sulfur vacancy enriched MoS<sub>2</sub> nanosheets (V<sub>S</sub>-MoS<sub>2</sub>) with BiVO<sub>4</sub> nanocrystals through electrostatic selfassembly for photocatalytic N2 reduction. Under simulated sunlight irradiation (100 mW cm<sup>-2</sup>), BiVO<sub>4</sub>/V<sub>s</sub>-MoS<sub>2</sub> exhibits efficient photocatalytic N2 reduction activity, with a NH3 yield of 132.8  $\mu$ mol g<sup>-1</sup> h<sup>-1</sup>, nearly 7 times that of pure V<sub>s</sub>-MoS<sub>2</sub> (20  $\mu$ mol g<sup>-1</sup> h<sup>-1</sup>). In addition, the experimental results from *in situ* X-ray photoelectron spectroscopy and electron spin resonance spectroscopy verify the presence of sulfur-rich vacancies on the surface of V<sub>8</sub>-MoS<sub>2</sub> nanosheets and the successful formation of an S-scheme heterojunction, which are conducive to the improvement of N2 adsorption-activation and driving force of water oxidation as well as charge separation. The mechanism of the N<sub>2</sub> reduction reaction is speculated using in situ diffuse reflectance infrared Fourier transform spectroscopy.

## 2. Experimental

### 2.1. Sample preparation

2.1.1. Preparation of V<sub>S</sub>-MoS<sub>2</sub> nanosheets. Na<sub>2</sub>MoO<sub>4</sub>·2H<sub>2</sub>O (243 mg) and CH<sub>4</sub>N<sub>2</sub>S (304 mg) were dissolved in ultrapure water (35 mL). After 30 min of stirring, the mixture was transferred to a 50 mL Teflon autoclave and heated at 180 °C for 48 h. Subsequently, the products were washed 3 times with a 0.1 M HCl solution to eliminate any residual nitrogen in the sample. The V<sub>S</sub>-MoS<sub>2</sub> nanosheet powder can be obtained after vacuum drying at 60 °C for 12 h.

**2.1.2. Preparation of BiVO<sub>4</sub> nanocrystals.** In a three-neck flask, a mixture containing 484 mg of  $Bi(NO_3)_3 \cdot 5H_2O$ , 20 mL of octadecene, 3 mL of oleylamine, and 3 mL of oleic acid was heated to 170 °C until it became transparent, and then stored at 100 °C. NaVO<sub>3</sub> (242 mg) was dissolved in ultrapure water (20 mL) at 100 °C, and added to the above three-neck flask. The resulting mixture was poured into ethanol to induce precipitation. Afterward, it was subjected to three rounds of washing with a hexane and ethanol mixture, followed by vacuum drying at 60 °C for 12 h to obtain a yellow-green BiVO<sub>4</sub> nanocrystal. For further purification, the obtained BiVO<sub>4</sub> quantum dots (20 mg) were dispersed in a solution comprising 10 mL of isopropanol

and 1 mL of KI in DMSO (0.1 M). Ultrasonic treatment was performed for 10 min to remove the ligands introduced during the synthesis process and prevent their interference in the photocatalytic  $N_2$  fixation experiment.

**2.1.3. Preparation of BiVO**<sub>4</sub>/V<sub>S</sub>-**MoS**<sub>2</sub>. V<sub>S</sub>-MoS<sub>2</sub> nanosheets (30 mg) and BiVO<sub>4</sub> nanocrystals (10 mg) were dispersed in toluene (10 mL). The mixture was ultrasonicated for 10 min and stirred for 3 h in the dark. The suspension was centrifuged followed by washing 3 times with hexane. The BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> heterojunction can be obtained after vacuum drying at 60 °C for 12 h. In addition, a series of samples can be obtained by adjusting the mass ratio of BiVO<sub>4</sub> and V<sub>S</sub>-MoS<sub>2</sub> as 10 mg : 10 mg, 10 mg : 20 mg, 10 mg : 40 mg, denoted as BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> (1/1), BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> (1/2) and BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> (1/4), respectively.

### 2.2. Photocatalytic N<sub>2</sub> reduction experiment

The photocatalytic N<sub>2</sub> reduction reactions were carried out in a gas–solid reaction system (25 °C). 20 mg of photocatalyst was placed on the sample table of the reactor. 200  $\mu$ L of water was injected into the bottom of the reactor as the proton source. Before initiating the photocatalytic reactions, the system was heated to produce water vapor. The system was meticulously degassed to remove air with N<sub>2</sub> (99.999%), where N<sub>2</sub> was bubbled through 1 M HCl as well as a mixed solution of potassium permanganate and KOH to ensure the removal of potential contaminants. A 300 W xenon lamp equipped with a UVVISCUT400 filter was employed as the light source (light intensity of 100 mW cm<sup>-2</sup>). For detection, 2 mL of H<sub>2</sub>O was injected into the system to dissolve the product to form the product solution.

### 2.3. Product detection

**2.3.1.** Detection of  $NH_4^+$ . The  $NH_4^+$  concentration was determined with the indophenol blue method as follows: three chromogenic solutions were first prepared, divided into chromogenic agent A, chromogenic agent B, and chromogenic agent C. Chromogenic agent A was prepared by mixing NaOH (4 g), salicylic acid (5 g), and sodium citrate (5 g); chromogenic agent B was obtained by preparing a 0.05 M NaClO aqueous solution; chromogenic agent C was prepared by using 0.1 g sodium nitroferricyanide solution. The product solution (2 mL) was mixed with reagent A (2 mL), reagent B (1 mL), and reagent C (200  $\mu$ L), and then left for two hours to be detected. Finally, the absorbance at a wavelength of 655 nm was measured to quantify the  $NH_4^+$  content according to the established standard curve of the  $NH_4Cl$  solution.

**2.3.2.** Detection of  $NO_3^-$ . The specific process is as follows: first, prepare 1.0 ppm, 0.5 ppm, 0.2 ppm, and 0.1 ppm solutions of NaNO<sub>3</sub> as the standard solutions to establish the standard curve. Then, the reaction solution (2 mL) was detected by using a model NEXION300 ion chromatograph.

**2.3.3.** Detection of  $NO_2^-$ . The colorimetric method for the detection of  $NO_2^-$  concentration is as follows: color reagent A was prepared by dissolving sulfonamide (0.5 g) in 50 mL of HCl solution (2 M); color reagent B was prepared by dissolving *N*-(1-naphthyl) ethylenediamine hydrochloride (20 mg) in 20 mL of

ultrapure water. The reaction solution (2 mL) was mixed with color reagent A (40  $\mu$ L) and color reagent B (40  $\mu$ L), and then left in the dark for 10 min. The absorbance was characterized by UV-vis absorption spectroscopy, and the content of NO<sub>2</sub><sup>-</sup> was quantified according to the established standard curve at a wavelength of 540 nm.

**2.3.4.** Detection of  $N_2H_4$ . The Watt–Chrisp method was employed to determine the concentration of hydrazine hydrate as follows: the color reagent was prepared by mixing *N*,*N*-dimethyl-4-aminobenzaldehyde (2 g), concentrated HCl (10 mL), and ethanol (100 mL). The reaction solution (2 mL) was mixed with the color reagent (2 mL), and then left in the dark for 15 min. The absorbance at ~458 nm was obtained, and the content of  $N_2H_4$  was quantified according to the established standard curve.

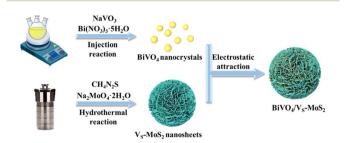
# 2.4. *In situ* diffuse reflectance infrared Fourier transform spectra (DRIFTS)

In situ diffuse reflectance infrared Fourier transform spectra were recorded using a Bruker IFS 66v Fourier transform spectrometer. The samples were mixed with KBr in a quartz mortar and then placed in an infrared reaction chamber. Pure N<sub>2</sub> (99.999%) containing water vapor was continuously introduced into the experimental chamber during *in situ* characterization. The IR spectrum of pure KBr was first collected as a background spectrum. The final spectra were obtained by subtracting the background spectrum from the spectrum of the sample.

## 3. Results and discussion

## 3.1. Preparation and structure of BiVO<sub>4</sub>/V<sub>s</sub>-MoS<sub>2</sub>

The synthetic process of BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> is illustrated in Scheme 1. Briefly, V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub> were initially prepared through the hydrothermal method and thermal injection method, respectively. The measured zeta potential ( $\zeta$ ) of V<sub>S</sub>-MoS<sub>2</sub> is negative (-45 mV), opposited with that of BiVO<sub>4</sub> (33 mV) in toluene (Fig. S1†). This opposite surface charging characteristic of V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub> should facilitate the spontaneous assembly to form BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> in solution. X-ray diffraction (XRD) patterns (Fig. 1a) show that the as-prepared V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub> can be indexed to the *P*63/*mmc*(194) hexagonal space group (PDF card no. 01-075-1539) and *I*2/*a*(15) monoclinic space group (PDF card no. 00-014-0688),



 $\mbox{Scheme 1}$   $\mbox{Scheme 1}$   $\mbox{Scheme 1}$   $\mbox{Scheme 1}$   $\mbox{Scheme 1}$   $\mbox{V}_{S}\mbox{-MoS}_{2}.$ 

respectively. The characteristic diffraction peaks at 14.39°,  $32.8^\circ$ ,  $39.65^\circ$  and  $58.56^\circ$  of V<sub>S</sub>-MoS<sub>2</sub> correspond to the (002), (100), (103), and (110) crystal planes. The diffraction peaks of BiVO<sub>4</sub> are located at 18.67°, 28.95°, 35.22°, 39.78°, 46.71°, 49.96°, and 59.26°, corresponding to the (110), (121), (002), (211), (240), (-202), and (123) crystal planes. Notably, the diffraction pattern of BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> contains the characteristic peaks of both  $V_{s}$ -MoS<sub>2</sub> and BiVO<sub>4</sub>, indicating the successful loading of BiVO4 nanocrystals onto Vs-MoS2 nanosheets. Scanning electron microscopy (SEM) and transmission electron microscopy (TEM) measurements revealed that V<sub>s</sub>-MoS<sub>2</sub> exhibits a nanoflower morphology (Fig. 1b), which is formed by the gathering of nanosheets (Fig. 1c). Atomic force microscopy (AFM) analysis in Fig. S2<sup>†</sup> further confirmed that V<sub>S</sub>-MoS<sub>2</sub> has a nanosheet morphology with a mean thickness of  $\sim$ 3 nm. TEM images of pure BiVO4 and BiVO4/V8-MoS2 (Fig. 1d and e) show that BiVO<sub>4</sub> nanocrystals are interspersed on V<sub>S</sub>-MoS<sub>2</sub> nanosheets, with an average size of  $\sim$ 5 nm, which is almost identical to that of the pure BiVO<sub>4</sub> nanocrystal (Fig. S3<sup>†</sup>). Further highresolution TEM (HRTEM) analysis (Fig. 1f) showed clear lattice fringes of 2.72 Å and 3.08 Å, corresponding to the (100) plane of V<sub>S</sub>-MoS<sub>2</sub> (ref. 35) and the (121) plane of monoclinic  $BiVO_4$  (ref. 36) (Fig. S4<sup>†</sup>), respectively, confirming the presence of BiVO<sub>4</sub> nanocrystals on the surface of V<sub>S</sub>-MoS<sub>2</sub> nanosheets. The corresponding energy-dispersive X-ray spectroscopy (EDS) mapping analysis (Fig. 1g) demonstrated the homogeneous distribution of Mo, S, Bi, V, and O elements on BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub>, further verifying the construction of BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub>.

To gain insights into the structural characteristics of the asprepared photocatalysts, electron paramagnetic resonance (EPR) measurements were performed initially. As depicted in Fig. 1h, a distinct EPR signal at g = 2.003 can be recognized for  $V_{S}$ -MoS<sub>2</sub>, signifying the formation of the sulfur vacancies on the surface of V<sub>S</sub>-MoS<sub>2</sub>.<sup>37</sup> In the case of BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub>, a stronger EPR signal is detected, providing evidence for the formation of heterojunction interfaces, which can turn spin-coupled electron pairs into unpaired electron states.38 Sulfur vacancies can serve as active sites to promote carrier capture and N<sub>2</sub> adsorption and activation.39 The X-ray photoelectron spectra (XPS) were further analyzed to investigate the potential interfacial interaction and charge transfer processes within the BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> heterojunction. Doublet XPS characteristic peaks can be identified at 229.3 eV and 232.4 eV in pure V<sub>S</sub>-MoS<sub>2</sub>, attributed to Mo 3d<sub>5/2</sub> and Mo  $3d_{3/2}$  (Fig. S5a<sup>†</sup>), which can confirm the reduction of Mo<sup>6+</sup> to Mo<sup>4+</sup> during the growth of V<sub>S</sub>-MoS<sub>2</sub> nanosheets.<sup>40</sup> In addition, a comparison between pure V<sub>S</sub>-MoS<sub>2</sub>, BiVO<sub>4</sub>, and BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> reveals noticeable shifts in binding energy for Mo 3d, S 2p, Bi 4f, and V 2p. Specifically, Mo 3d and S 2p exhibit positive shifts of 0.50 eV and 0.20 eV, while Bi 4f and V 2p display negative shifts of 0.20 eV and 0.20 eV, respectively (Fig. S5b–d<sup>†</sup>). These charge redistributions within the BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> heterojunction reflect a strong chemical interaction at the interface of the BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> heterojunction. This robust interfacial electronic coupling in BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> is expected to facilitate the charge transfer between the V<sub>S</sub>-MoS<sub>2</sub> nanosheets and BiVO<sub>4</sub> nanocrystals.

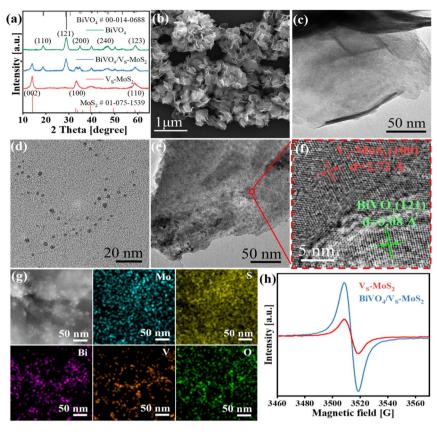


Fig. 1 (a) XRD patterns of  $V_s$ -MoS<sub>2</sub>, BiVO<sub>4</sub>, and BiVO<sub>4</sub>/ $V_s$ -MoS<sub>2</sub>. (b and c) SEM and TEM images of a  $V_s$ -MoS<sub>2</sub> nanosheet. (d) TEM image of a BiVO<sub>4</sub> nanocrystal. (e-g) TEM, HRTEM, and corresponding EDS images of BiVO<sub>4</sub>/ $V_s$ -MoS<sub>2</sub>. (h) EPR spectra of  $V_s$ -MoS<sub>2</sub> and BiVO<sub>4</sub>/ $V_s$ -MoS<sub>2</sub>.

# 3.2. S-scheme mechanism of the $BiVO_4/V_S-MoS_2$ heterojunction

The energy levels and interfacial charge transfer processes of  $BiVO_4/V_8$ -MoS<sub>2</sub> were explored to evaluate the photocatalytic N<sub>2</sub> reduction potential of the as-prepared photocatalysts. Fig. 2a and b show the UV-vis diffuse reflectance spectra (DRS), revealing a good light response for both the V<sub>S</sub>-MoS<sub>2</sub> nanosheets and BiVO<sub>4</sub> nanocrystals. From the corresponding Tauc plots (insets of Fig. 2a and b), the band gaps  $(E_{g})$  of V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub> can be deduced to be 1.71 eV and 2.22 eV, respectively. To ascertain the energy band structures of V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub>, the onset edge  $(E_i)$  and the secondary electron cutoff  $(E_{cutoff})$  were determined by carrying out ultraviolet photoelectron spectroscopy (UPS) (Fig. 2c). According to the equation  $E_{VB} = 21.22$  –  $(E_{\rm cutoff} - E_{\rm i})$ , the valence band edge potentials  $(E_{\rm VB})$  can be calculated to be 1.35 V and 2.23 V versus the standard hydrogen electrode (vs. NHE) for V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub>, respectively. By combining the values from  $E_{\rm g}$  and  $E_{\rm VB}$  analysis, the corresponding conduction band edge potentials  $(E_{CB})$  can be calculated to be -0.36 V and 0.01 V (vs. NHE) for V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub>, respectively. The resultant energy band structures of Vs-MoS2 and BiVO<sub>4</sub> are presented in Fig. 2d. The photogenerated electrons in V<sub>S</sub>-MoS<sub>2</sub> possess sufficient energy to drive the photoreduction of N<sub>2</sub> to NH<sub>3</sub> (-0.13 V vs. NHE),<sup>41</sup> while their driving force for H<sub>2</sub>O oxidation is relatively weak. Meanwhile, the photogenerated holes in BiVO<sub>4</sub> can trigger H<sub>2</sub>O photooxidation

to  $O_2$  (0.82 V vs. NHE, pH = 7), while they are insufficient for the photoreduction of N2. In addition, the Fermi levels were also estimated according to the UPS spectra, to be -4.62 eV and -5.27 eV (vs. vacuum) for V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub>, respectively. These results reveal that both V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub> are n-type semiconductors, consistent with the results from the Mott-Schottky tests, where the slopes of Mott-Schottky curves for both  $BiVO_4$  and  $V_8$ -MoS<sub>2</sub> are positive (Fig. S6<sup>†</sup>). From the above results and analysis, we can preliminarily deduce that, given the higher Fermi level of V<sub>S</sub>-MoS<sub>2</sub> compared to that of BiVO<sub>4</sub>, the free electrons in V<sub>S</sub>-MoS<sub>2</sub> would spontaneously flow to BiVO<sub>4</sub> to establish a Fermi level equilibrium upon contact (Fig. S7(I-II)†). A built-in electric field and band bending of the interface in BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> would be formed. Driven by the interfacial builtin electric field, photogenerated electrons in BiVO4 would recombine with the photogenerated holes in Vs-MoS2 (Fig. S7(III)<sup>†</sup>), facilitating the formation of the S-scheme charge transfer pathway.

To scrutinize the S-scheme charge transfer pathway in the  $BiVO_4/V_S-MOS_2$  heterojunction, *in situ* irradiated XPS (ISI-XPS) spectra were first measured to detect photoinduced changes in the electron cloud density around the nuclei of elements. As depicted in Fig. S8a and b,† the binding energies of Mo 3d and V 2p in  $BiVO_4/V_S-MOS_2$  demonstrate a negative displacement (~0.40 eV) and positive movement (~0.30 eV) under illumination, respectively, compared with those in the dark. These

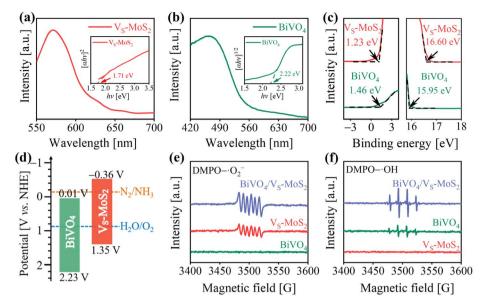


Fig. 2 (a and b) UV-vis DRS spectra of V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub>. The insets show the corresponding Tauc plots. (c) UPS spectra of V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub>. (d) Energy band structures of V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub> (pH = 7). EPR signals of (e) DMPO- $\cdot$ O<sub>2</sub><sup>-</sup> and (f) DMPO- $\cdot$ OH over V<sub>S</sub>-MoS<sub>2</sub>, BiVO<sub>4</sub>, and BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> under illumination.

binding energy changes indicate the accumulation of photogenerated electrons on V<sub>S</sub>-MoS<sub>2</sub> and photogenerated holes on BiVO<sub>4</sub>, revealing the occurrence of S-scheme interfacial charge transfer within the BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> heterojunction. To further confirm this S-scheme interfacial charge transfer mechanism in the  $BiVO_4/V_8$ -MoS<sub>2</sub> heterojunction, the EPR spectra were recorded using 5,5-dimethyl-1-pyrroline N-oxide (DMPO) as the trapping agent.<sup>42</sup> In the case of pure V<sub>S</sub>-MoS<sub>2</sub>, only the DMPO-·  $O_2^-$  characteristic signal can be identified (Fig. 2e), as its  $E_{VB}$ potential is insufficient to drive the oxidation of  $H_2O$  to  $\cdot OH$ . Conversely, in pure BiVO<sub>4</sub>, only the DMPO-·OH characteristic signal can be recognized (Fig. 2f), due to the insufficient driving force of photogenerated electrons in  $E_{\rm CB}$  to trigger the reduction of  $O_2$  to  $\cdot O_2^-$  (-0.33 V vs. NHE). For the BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> heterojunction, more obvious DMPO-·O2<sup>-</sup> and DMPO-·OH signals can be simultaneously identified, providing compelling evidence for the establishment of an interfacial S-scheme charge transport channel. That is to say, the photogenerated electrons in BiVO<sub>4</sub> and the photogenerated holes in V<sub>s</sub>-MoS<sub>2</sub> initially recombine through the interfacial S-scheme channel, leading to the accumulation of photogenerated holes on BiVO<sub>4</sub> and photogenerated electrons on V<sub>s</sub>-MoS<sub>2</sub>. This spatial separation of charge carriers in the BiVO<sub>4</sub>/V<sub>8</sub>-MoS<sub>2</sub> heterojunction would more effectively promote their participation in the redox reaction.

#### 3.3. Photogenerated carrier evolution

In general, the evolution of photogenerated charges within photocatalysts plays a pivotal role in determining their photocatalytic activity.<sup>43,44</sup> To evaluate the behavior of photogenerated carriers in BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub>, steady-state photoluminescence (PL) spectrum measurements were first performed. As presented in Fig. 3a, the PL spectrum of BiVO<sub>4</sub> displays an intrinsic emission

band at  $\sim$ 490 nm under 365 nm excitation, which is related to photogenerated electron-hole recombination. Upon the construction of the BiVO4/Vs-MoS2 heterojunction, the PL spectrum exhibits significant quenching, indicating the effective transfer of photogenerated carriers between the BiVO<sub>4</sub> nanocrystals and V<sub>8</sub>-MoS<sub>2</sub> nanosheets. In addition, the photoelectrochemical properties of the samples were characterized to assess the potential positive influence of the construction of a heterostructure on charge evolution behavior. Notably, under light irradiation, BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> exhibits a smaller chargetransport resistance compared with both pure BiVO<sub>4</sub> and V<sub>S</sub>- $MoS_2$  (Fig. 3b and Table S1<sup>+</sup>), indicating that the construction of the electric field in the heterojunction improves the charge transport characteristics. From the transient photocurrent (I-t)measurements (Fig. 3c), it is evident that BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> has a higher current density than both  $BiVO_4$  and  $V_s$ -MoS<sub>2</sub>, providing further evidence of expedited charge separation kinetics within the BiVO4/V5-MoS2 heterojunction. Moreover, to more intuitively reveal the space charge separation, Kelvin probe force microscopy (KPFM) was utilized to measure the surface photovoltage (SPV) response of photocatalysts under light. Atomic force microscope (AFM) images (Fig. 3d and f) present the morphology outline of V<sub>S</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> nanosheet clusters, which are basically consistent with the SEM results (Fig. 1b). Under illumination, the SPV response zone (Fig. 3e and g) emerges, aligning with the morphology outlines of the samples. These observations also indicate the spatial charge separation and redistribution after light irradiation.45 As shown in Fig. 3h, pure V<sub>S</sub>-MoS<sub>2</sub> presents a feeble SPV signal under light irradiation, primarily due to rapid photogenerated carrier recombination. Benefiting from the construction of heterojunctions, BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> displays a noticeable enhancement of the SPV response, of ~100 mV, far surpassing



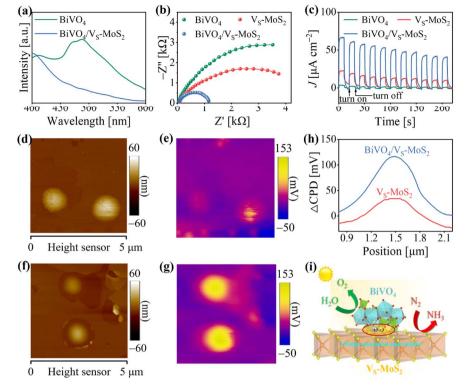


Fig. 3 (a) Steady-state photoluminescence spectra of BiVO<sub>4</sub> and BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub>. (b and c) EIS plots and *I*-t curves of BiVO<sub>4</sub>, V<sub>5</sub>-MoS<sub>2</sub>, and BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub> plotted at a bias potential of -0.4 V vs. Ag/AgCl. AFM height images of (d) V<sub>5</sub>-MoS<sub>2</sub> and (f) BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub>. SPV images of (e) V<sub>5</sub>-MoS<sub>2</sub> and (g) BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub> under illumination. (h) Potential difference changes ( $\Delta$ CPD) of V<sub>5</sub>-MoS<sub>2</sub> and BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub> by subtracting the potential under dark conditions from that under illumination. (i) Schematic illustration of the photogenerated carrier separation.

that of pure  $V_S$ -MoS<sub>2</sub>. Ultimately, these characterization studies underscore that the construction of heterojunctions can promote charge separation, and enhance the accumulation of electrons/holes on  $V_S$ -MoS<sub>2</sub> and BiVO<sub>4</sub>, respectively, which is beneficial for these carriers to participate in the subsequent multi-electron transfer processes during the photoreduction  $N_2$ reaction (Fig. 3i).

### 3.4. Photocatalytic N<sub>2</sub> reduction activity

The photocatalytic N2 reduction reactions were conducted in a gas-solid reaction apparatus (Fig. S9<sup>†</sup>) containing N<sub>2</sub> and H<sub>2</sub>O vapor under simulated sunlight irradiation (100 mW cm<sup>-2</sup>). To ensure the accuracy of our experiments, the samples were pretreated with a DMSO solution of KI. This step is crucial to remove any residual ligands introduced during the synthesis process, preventing any interference with the experimental results (Fig. S10,† details are described in the Experimental section). The photocatalytic activities were evaluated by evaluating the NH<sub>4</sub><sup>+</sup> production using the indophenol blue method (Fig. S11,<sup>†</sup> details are described in the Experimental section).<sup>46</sup> As illustrated in Fig. S12,<sup>†</sup> a prominent absorption signal at  $\sim$ 655 nm can be observed, indicating that N<sub>2</sub> is effectively photoreduced to NH3 in the presence of light for BiVO4/Vs-MoS<sub>2</sub>. The NH<sub>3</sub> generation performances for the as-prepared photocatalysts are presented in Fig. 4a and S13.† For pure BiVO<sub>4</sub>, there is virtually no NH<sub>3</sub> synthesis activity due to the

insufficient driving force of electron energy in its conduction band (Fig. 2d). Meanwhile, V<sub>S</sub>-MoS<sub>2</sub> exhibits a weak N<sub>2</sub> photoreduction to NH<sub>3</sub> activity, with a rate of  $20.0 \pm 1.1 \,\mu\text{mol g}^{-1} \,\text{h}^{-1}$ , resulting from its insufficient thermodynamic driving force for H<sub>2</sub>O oxidation and serious charge recombination. Upon combining the V<sub>S</sub>-MoS<sub>2</sub> nanosheets with the BiVO<sub>4</sub> nanocrystals, the corresponding photocatalytic N2 reduction activity improves significantly, reaching 132.8  $\pm$  4.2  $\mu$ mol g<sup>-1</sup> h<sup>-1</sup> within 4 hours, which is nearly 7-fold that of pure V<sub>s</sub>-MoS<sub>2</sub>. The apparent quantum efficiency at 575 nm can reach 0.3% (Fig. S14<sup> $\dagger$ </sup>). Certainly, we also analyzed the NH<sub>4</sub><sup>+</sup> production by ion chromatography (Fig. S15<sup>†</sup>), and the results are in agreement with those obtained by the indophenol blue method. Obviously, this improvement of NH<sub>3</sub> evolution activity can be attributed to the increased driving force for water oxidation and the enhanced separation of photogenerated carriers in the BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> heterojunction, compared with pure V<sub>S</sub>-MoS<sub>2</sub> nanosheets. By adjusting the mass ratio of BiVO<sub>4</sub> and V<sub>S</sub>-MoS<sub>2</sub> (Fig. S16<sup> $\dagger$ </sup>), the NH<sub>3</sub> evolution activities of the samples were screened, in which BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> with a mass ratio (BiVO<sub>4</sub> : V<sub>S</sub>- $MoS_2$ ) of 1 : 3 exhibits the best performance (Fig. 4a).

Moreover, the O<sub>2</sub> evolution activity of BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> was also measured through a gas chromatograph, to be 110.0  $\pm$  4.5 µmol g<sup>-1</sup> h<sup>-1</sup> (Fig. S17†). This result suggests that the rate of consumed electrons ( $R_{\text{electron}}$ ) for N<sub>2</sub> reduction to NH<sub>3</sub> is nearly equal to the rate of consumed holes ( $R_{\text{hole}}$ ) for water oxidation to O<sub>2</sub>, in accordance with the formulae of  $R_{\text{elecron}} = 3 \times R_{\text{NH}_3}$  and

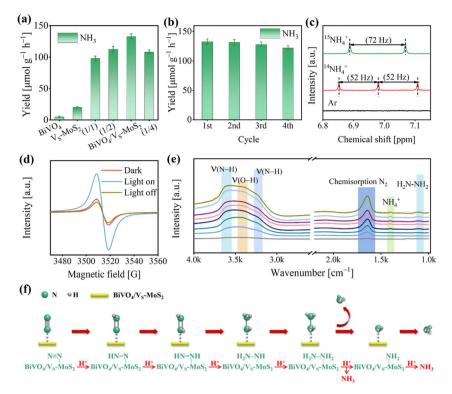


Fig. 4 (a) Photocatalytic NH<sub>3</sub> production rates for BiVO<sub>4</sub>, V<sub>5</sub>-MoS<sub>2</sub>, BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub>, BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub> (1/1), BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub> (1/2), and BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub> (1/4) under 4 h light irradiation. (b) NH<sub>3</sub> synthesis for four cyclic tests of BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub>. (c) The <sup>1</sup>H NMR spectra of products with <sup>14</sup>N<sub>2</sub> or <sup>15</sup>N<sub>2</sub> as the reaction atmosphere. (d) *In situ* EPR spectra of BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub> in the dark or under light irradiation in a N<sub>2</sub> atmosphere or light off in a N<sub>2</sub> atmosphere. (e) *In situ* DRIFTS spectra of the photoreduction N<sub>2</sub> reaction. (f) The proposed reaction pathway of the photoreduction N<sub>2</sub> reaction.

 $R_{\text{hole}} = 4 \times R_{\text{O}_2}$ . This balance signifies the effective utilization of the photogenerated electrons and holes. Based on the above analysis, the whole photocatalytic reaction including N<sub>2</sub> reduction and H<sub>2</sub>O oxidation by BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub> can be described as 2N<sub>2</sub> + 6H<sub>2</sub>O  $\rightarrow$  4NH<sub>3</sub> + 3O<sub>2</sub>. Additionally, the robustness of BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub> was evaluated by reemploying the photocatalyst in four cycles of tests (Fig. 4b), which reveals little decrement in activity. In addition, the XRD patterns (Fig. S18†) and TEM images (Fig. S19†) of BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub> after the photocatalytic reaction exhibit no obvious changes, confirming the good stability of the photocatalyst in this gas–solid photocatalytic system. The Mo 3d and Bi 4f XPS spectra of BiVO<sub>4</sub>/V<sub>5</sub>-MoS<sub>2</sub> after catalysis show almost no significant changes, further suggesting the maintenance of the local coordination environment of the Bi and Mo sites.

To elucidate the origin of NH<sub>3</sub> and O<sub>2</sub> during the photocatalytic reaction, several controlled experiments were carried out using BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> as the photocatalyst (Fig. S21†). In the absence of a photocatalyst (BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub>), N<sub>2</sub>, light, or H<sub>2</sub>O, there is nearly no NH<sub>3</sub> evolution, unequivocally demonstrating that the N<sub>2</sub> reduction reaction is indeed a photocatalytic reaction using BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> as the photocatalyst with H<sub>2</sub>O as the proton source. According to the characterization by the colorimetric method and ion chromatography (the details are described in the Experimental section), nearly no NO<sub>2</sub><sup>-</sup> and NO<sub>3</sub><sup>-</sup> signals in the product system can be detected before and

after the photocatalytic reaction (Fig. S22 and S23<sup>†</sup>). In addition, we have further measured the N content in the obtained photocatalyst by EDS analysis (Fig. S24 and Table S2†), and no N atoms are present. These results confirm that NH<sub>3</sub> remained unoxidized, and substantiate that NH<sub>3</sub> originated solely from N<sub>2</sub> reduction, excluding impurity conversion as a source. To further verify the origin of NH<sub>3</sub> in the product system, isotope labeling experiments were performed using BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> as the photocatalyst in atmospheres containing <sup>15</sup>N<sub>2</sub>, <sup>14</sup>N<sub>2</sub>, or Ar, respectively (Fig. S25<sup>+</sup>). More specifically, no NH<sub>4</sub><sup>+</sup> signal is detected under a Ar atmosphere in the nuclear magnetic resonance (NMR) spectra, while distinct signals belonging to <sup>15</sup>NH<sub>4</sub><sup>+</sup> or  ${}^{14}NH_4^+$  can be observed in a  ${}^{15}N_2$  or  ${}^{14}N_2$  atmosphere, respectively (Fig. 4c). These results directly confirm that NH<sub>4</sub><sup>+</sup> is indeed generated from the N<sub>2</sub> in the system. In addition, the mass spectrometry analysis of the product (Fig. S26<sup>†</sup>) was also performed, revealing an  ${}^{18}O_2$  signal at m/z = 36, which confirms that  $O_2$  is produced from  $H_2O$  oxidation.

To gain insight into the photocatalytic  $N_2$  reduction process of the BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> heterojunction, we conducted further characterization to explore the active sites and monitor the evolution of intermediates during the photocatalytic reaction, by using *in situ* EPR spectra and *in situ* diffuse reflectance infrared Fourier transform spectra (DRIFTS), respectively. As presented in Fig. 4d, the intensity of the sulfur vacancy signal for BiVO<sub>4</sub>/V<sub>S</sub>-MoS<sub>2</sub> exhibits an increment when exposed to light

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irradiation for 15 min, and decreases once the light was turned off for 10 min, suggesting that the sulfur vacancies facilitate the trapping of photogenerated electrons from the conduction band.47,48 The exposed Mo site at the sulfur vacancy is in a coordination unsaturated state, and can act as the photocatalytic active site bonding with N2. The trapped photogenerated electrons at sulfur vacancies can transfer to N<sub>2</sub> molecules to achieve N<sub>2</sub> reduction and transformation. As the photocatalytic N2 reduction reaction proceeded, a series of absorption signals were detected belonging to intermediates adsorbed on BiVO<sub>4</sub>/V<sub>s</sub>-MoS<sub>2</sub> (Fig. 4e). Specifically, an obvious peak at 1648 cm<sup>-1</sup> belonging to the chemisorbed N<sub>2</sub> (-N $\equiv$ N) appeared,<sup>49</sup> which can be attributed to the efficient adsorption and activation of N<sub>2</sub> by the Mo sites at the vacancies of the nanosheets.<sup>50</sup> The peak at 3432 cm<sup>-1</sup> is attributed to  $\nu$ (O-H) of  $H_2O$ , which serves as the proton source for  $N_2$  activation. The overlapped signal bands at 3230 cm<sup>-1</sup> and 3555 cm<sup>-1</sup> can be attributed to  $\nu$ (N–H) stretching modes of NH<sub>3</sub>, and the peak at 1403  $\text{cm}^{-1}$  can be attributed to  $\text{NH}_4^+$  adsorption. The enhancement of these characteristic signals implies the progression of N2 activation and conversion to NH3 via a multistep proton-coupled electron transfer (PCET) process over  $BiVO_4/V_s$ -MoS<sub>2</sub>. In addition, a peak at 1102 cm<sup>-1</sup> can be identified, originating from the H2N-NH2 characteristic signal.<sup>51</sup> Given that there is no hydrazine formation in the product (Fig. S27<sup> $\dagger$ </sup>), we thus speculate that the photocatalytic N<sub>2</sub> fixation process on BiVO4/Vs-MoS2 follows an associative alternating pathway (Fig. 4f). In this pathway, hydrogenation occurs alternatively on two N atoms, with the final step involving the cleavage of the N-N bond to generate the first NH<sub>3</sub> molecule, followed by the last hydrogenation and another NH<sub>3</sub> desorption.

## 4. Conclusions

In summary, we have successfully prepared an S-scheme heterojunction of BiVO4/Vs-MoS2 by coupling the N2-activated component (Vs-MoS<sub>2</sub>) and the water-oxidized module (BiVO<sub>4</sub>) to facilitate the process of photocatalytic N2 reduction. BiVO4/Vs-MoS<sub>2</sub> exhibits efficient NH<sub>3</sub> synthesis activity using H<sub>2</sub>O as a proton source under illumination (100 mW cm<sup>-2</sup>), with an  $NH_3$  yield of 132.8  $\mu$ mol g<sup>-1</sup> h<sup>-1</sup>, nearly 7 times higher than that of pure V<sub>s</sub>-MoS<sub>2</sub>. Our experimental findings underscore the pivotal roles played by the V<sub>S</sub>-MoS<sub>2</sub> nanosheet with sulfur-rich vacancies in enhancing N2 adsorption and activation. Furthermore, the construction of the S-scheme heterojunction substantially elevates the driving force for H<sub>2</sub>O oxidation and significantly improves charge separation within the system. Moreover, an alternate association pathway for N<sub>2</sub> photoreduction reaction is proposed according to the in situ DRIFTS characterization. This study presents an efficient example for achieving the N2 conversion process under mild conditions.

## Author contributions

Han-Ying Luo: data curation, formal analysis, validation. Zhao-Lei Liu: data curation, formal analysis, validation. Meng-Ran Zhang: formal analysis, supervision. Yan-Fei Mu: validation, writing – original draft preparation, funding acquisition. Min Zhang: conceptualization, funding acquisition, supervision, validation, writing – reviewing and editing.

# Conflicts of interest

There are no conflicts of interest to declare.

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